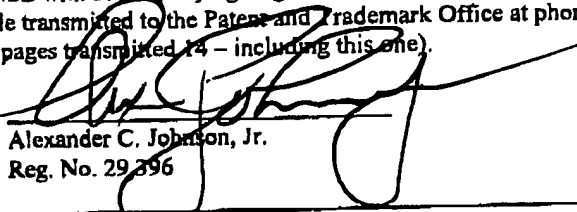


Certificate of Facsimile Transmission

I hereby certify that this SUPPLEMENTAL RESPONSE with accompanying English translation of Sakamoto (JP 03-109775) to Examiner S. Loke is being facsimile transmitted to the Patent and Trademark Office at phone No. (703)308-7722 on the date shown below. (Total pages transmitted 14 - including this one).

Dated: January 25, 2002


Alexander C. Johnson, Jr.
Reg. No. 29,396PATENT APPLICATION
Attorney's Do. No. 1138-71

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re divisional patent application of:

DAH WEN TSANG; JOHN W. MOSIER II, deceased;
DOUGLAS A. PIKE, JR. and
THEODORE O. MEYER

Examiner S. Loke

Serial No. 09/144,579

Group Art Unit 2811

Filed: August 31, 1998

For: SELF ALIGNED VERTICAL POWER MOSFET WITH
ENHANCED BASE REGIONAssistant Commissioner for Patents
Washington, D.C. 20231FAX COPY RECEIVED
JAN 25 2002
TECHNOLOGY CENTER 2800#15
Translation
FJONES
3-15-02**SUPPLEMENTAL RESPONSE**

Supplementing the amendment filed December 4, 2001, applicants respectfully request incorporation of further remarks as follows.

In the previous amendment, applicants presented remarks with reliance upon an English abstract and drawings of Laid-Open Japanese Patent 03-109775 of Sakamoto. Since filing the previous amendment of December 4, 2001, applicants obtained a translation of Sakamoto. A copy of this translation is enclosed for benefit of the Examiner. According to the translation, Sakamoto teaches forming a silicide on a polysilicon gate. In regards to the gate formation, Sakamoto and Korman teach essentially the same thing - i.e., forming silicide